L Number	Hits	Search Text	DB	Time stamp
- Namer	5301148		USPAT;	2004/09/06 15:38
	5551110	or si or polysi or polysilicon or (poly or	US-PGPUB;	
		polycrystal\$4) adj2 (si or silicon)	EPO; JPO;	1
<u> </u>			DERWENT;	
]			IBM_TDB	
-	922075	1	USPAT;	2004/09/06 15:37
		nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	
		fluorinat\$4	EPO; JPO;	
			DERWENT;	
_	53915/3	anneal\$4 or heat\$4 or treat\$4	USPAT;	2004/09/02 14:35
	3301343	anneary or nearly or creatly	US-PGPUB;	2004/03/02 11:33
	!		EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	9119385	oxygen or "o.sub.2" or "o" or hydrogen or	USPĀT;	2004/09/02 14:39
		"h.sub.2" or "h" or fluorine or "f.sub.2"	US-PGPUB;	
		or "f" or halogen	EPO; JPO;	
,			DERWENT;	
1	7070400		IBM_TDB	2004/00/06 15:20
-	7278429	sidewall or wall or side or spacer	USPAT; US-PGPUB;	2004/09/06 15:39
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	102865	(aluminum or al or copper or cu or silicon	USPĀT;	2004/09/02 15:04
		or si or polysi or polysilicon or (poly or	US-PGPUB;	
		polycrystal\$4) adj2 (si or silicon)) with	EPO; JPO;	
		((oxidi\$5 or oxidat\$4 or nitridi\$4 or	DERWENT;	
		nitridat\$4 or nitrided or hydrogenat\$4 or	IBM_TDB	
		fluorinat\$4) or (anneal\$4 or heat\$4 or		1
		treat\$4)) with (oxygen or "o.sub.2" or "o"		
		or hydrogen or "h.sub.2" or "h" or fluorine or "f.sub.2" or "f" or halogen)		
_	263608	_	USPAT;	2004/09/02 14:57
-	203000	or si or polysi or polysilicon or (poly or	US-PGPUB;	2001,03,02 14.3,
		polycrystal\$4) adj2 (si or silicon)) with	EPO; JPO;	
		(sidewall or wall or side or spacer)	DERWENT;	
		· · ·	IBM_TDB	
-	4456020	opening or hole or aperture	USPĀT;	2004/09/03 17:41
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
1_	17342	((aluminum or al or copper or cu or	USPAT;	2004/09/02 14:58
-	1/342	silicon or si or polysi or polysilicon or	US-PGPUB;	2301,03,02 14.00
1		(poly or polycrystal\$4) adj2 (si or	EPO; JPO;	
		silicon)) with ((oxidi\$5 or oxidat\$4 or	DERWENT;	
		nitridi\$4 or nitridat\$4 or nitrided or	IBM_TDB	
		hydrogenat\$4 or fluorinat\$4) or (anneal\$4	_	
		or heat\$4 or treat\$4)) with (oxygen or		
		"o.sub.2" or "o" or hydrogen or "h.sub.2"		
		or "h" or fluorine or "f.sub.2" or "f" or		
		halogen)) and ((aluminum or al or copper		
		or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4)		
		adj2 (si or silicon)) with (sidewall or		
		wall or side or spacer))		
_	39624		USPAT;	2004/09/02 15:05
		or si or polysi or polysilicon or (poly or	US-PGPUB;	
		polycrystal\$4) adj2 (si or silicon)) with	EPO; JPO;	
		(remov\$4 or etch\$4) with (opening or hole	DERWENT;	
		or aperture)	IBM_TDB	

	2868	(((aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with ((oxidi\$5 or oxidat\$4 or nitridi\$4 or nitridat\$4 or nitrided or hydrogenat\$4 or fluorinat\$4) or (anneal\$4 or heat\$4 or treat\$4)) with (oxygen or "o.sub.2" or "o" or hydrogen or "h.sub.2" or "h" or fluorine or "f.sub.2" or "f" or halogen)) and ((aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with (sidewall or wall or side or spacer))) and ((aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with (remov\$4 or etch\$4) with (opening or hole or aperture))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 15:04
_	146646	contact adj4 (opening or hole or aperture)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 17:43
-	10597	<pre>(aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with (remov\$4 or etch\$4) with (contact adj4 (opening or hole or aperture))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 15:07
	1036	(((aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with ((oxidi\$5 or oxidat\$4 or nitridi\$4 or nitridat\$4 or nitrided or hydrogenat\$4 or fluorinat\$4) or (anneal\$4 or heat\$4 or treat\$4)) with (oxygen or "o.sub.2" or "o" or hydrogen or "h.sub.2" or "h" or fluorine or "f.sub.2" or "f" or halogen)) and ((aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with (sidewall or wall or side or spacer))) and ((aluminum or al or copper or cu or silicon or si or polysi or polysilicon or (poly or polycrystal\$4) adj2 (si or silicon)) with (remov\$4 or etch\$4) with (contact adj4 (opening or hole or aperture)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 15:24
_	2002512	aluminum oxide or "al.sub.2 o.sub.3" or "al.sub.2o.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/02 15:26
-	1662540	oxide or dioxide or "sio" or "sio.sub.2" or nitride or "si.sub.3 n.sub.4" or "si.sub.3n.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 15:28
-	31880	copper near2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 15:28
-	2272440	(aluminum oxide or "al.sub.2 o.sub.3" or "al.sub.2o.sub.3") or (oxide or dioxide or "sio" or "sio.sub.2" or nitride or "si.sub.3 n.sub.4" or "si.sub.3n.sub.4") or (copper near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/02 15:31

	· · · · · · · · · · · · · · · · · · ·			
_	132644	(insulating or insulator or ((aluminum	USPAT;	2004/09/02 15:39
		oxide or "al.sub.2 o.sub.3" or "al.sub.2o.sub.3") or (oxide or dioxide or	US-PGPUB; EPO; JPO;	
		"sio" or "sio.sub.2" or nitride or	DERWENT;	
		"si.sub.3 n.sub.4" or "si.sub.3n.sub.4")	IBM TDB	
		or (copper near2 oxide))) with (sidewall	1501_155	
		or wall or side or spacer) with (aluminum		
		or al or copper or cu or silicon or si or		
		polysi or polysilicon or (poly or		
		polycrystal\$4) adj2 (si or silicon))		
-	2938	((aluminum or al or copper or cu or	USPAT;	2004/09/02 15:39
		silicon or si or polysi or polysilicon or	US-PGPUB;	
		(poly or polycrystal\$4) adj2 (si or	EPO; JPO;	
		silicon)) with ((oxidi\$5 or oxidat\$4 or	DERWENT;	
		nitridi\$4 or nitridat\$4 or nitrided or	IBM_TDB	
		hydrogenat\$4 or fluorinat\$4) or (anneal\$4		
	-	or heat\$4 or treat\$4)) with (oxygen or		
		"o.sub.2" or "o" or hydrogen or "h.sub.2" or "h" or fluorine or "f.sub.2" or "f" or		
		halogen)) same ((insulating or insulator	:	
		or ((aluminum oxide or "al.sub.2 o.sub.3"		
		or "al.sub.20.sub.3") or (oxide or dioxide		
		or "sio" or "sio.sub.2" or nitride or		
		"si.sub.3 n.sub.4" or "si.sub.3n.sub.4")		
		or (copper near2 oxide))) with (sidewall		
		or wall or side or spacer) with (aluminum		
		or al or copper or cu or silicon or si or		
		polysi or polysilicon or (poly or	•	
		polycrystal\$4) adj2 (si or silicon)))		
-	225	(((aluminum or al or copper or cu or	USPAT;	2004/09/02 16:11
		silicon or si or polysi or polysilicon or	US-PGPUB;	
		(poly or polycrystal\$4) adj2 (si or silicon)) with ((oxidi\$5 or oxidat\$4 or	EPO; JPO; DERWENT;	
		nitridi\$4 or nitridat\$4 or nitrided or	IBM TDB	
		hydrogenat\$4 or fluorinat\$4) or (anneal\$4	1011_100	
		or heat\$4 or treat\$4)) with (oxygen or	:	
		"o.sub.2" or "o" or hydrogen or "h.sub.2"		
		or "h" or fluorine or "f.sub.2" or "f" or		
		halogen)) same ((insulating or insulator		
		or ((aluminum oxide or "al.sub.2 o.sub.3"		
		or "al.sub.2o.sub.3") or (oxide or dioxide		
		or "sio" or "sio.sub.2" or nitride or	1	
		"si.sub.3 n.sub.4" or "si.sub.3n.sub.4")		
		or (copper near2 oxide))) with (sidewall or wall or side or spacer) with (aluminum	:	
		or al or copper or cu or silicon or si or		
		polysi or polysilicon or (poly or		
		polycrystal\$4) adj2 (si or silicon)))) and		
		((aluminum or al or copper or cu or		
		silicon or si or polysi or polysilicon or		
		(poly or polycrystal\$4) adj2 (si or		
		silicon)) with (remov\$4 or etch\$4) with		
		(contact adj4 (opening or hole or		
		aperture)))	Hanr	2004/00/00 16 27
-	552	438/666.ccls.	USPAT;	2004/09/02 16:17
			US-PGPUB;	
			EPO; JPO; DERWENT;	
	1		IBM TDB	
_	27455	 patterned adj3 (conductor or conductive or	USPAT;	2004/09/02 16:20
		metal or (aluminum or al or copper or cu	US-PGPUB;	
		or silicon or si or polysi or polysilicon	EPO; JPO;	
		or (poly or polycrystal\$4) adj2 (si or	DERWENT;	
		silicon)))	IBM_TDB	
-	2396779	transform\$4 or convert\$4	USPĀT;	2004/09/02 16:20
			US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	
	1		IBM TDB	

-	7255255	(oxidi\$5 or oxidat\$4 or nitridi\$4 or	USPAT;	2004/09/02 16:24
		nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	
		fluorinat\$4) or (anneal\$4 or heat\$4 or	EPO; JPO;	
		treat\$4) or (transform\$4 or convert\$4)	DERWENT;	
			IBM_TDB	
-	2477	((oxidi\$5 or oxidat\$4 or nitridi\$4 or	USPAT;	2004/09/02 16:25
		nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	
		fluorinat\$4) or (anneal\$4 or heat\$4 or	EPO; JPO;	
		treat\$4) or (transform\$4 or convert\$4))	DERWENT;	
		with (patterned adj3 (conductor or	IBM_TDB	
		conductive or metal or (aluminum or al or		
		copper or cu or silicon or si or polysi or		
		polysilicon or (poly or polycrystal\$4)		
		adj2 (si or silicon))))		
-	559		USPAT;	2004/09/02 16:26
		nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	
		fluorinat\$4) or (anneal\$4 or heat\$4 or	EPO; JPO;	
	1	treat\$4) or (transform\$4 or convert\$4))	DERWENT;	
		with (patterned adj3 (conductor or	IBM_TDB	
		conductive or metal or (aluminum or al or		
		copper or cu or silicon or si or polysi or		
		polysilicon or (poly or polycrystal\$4)		
		adj2 (si or silicon))))) and (contact adj4		
_	100	(opening or hole or aperture)) 438/635.ccls.	Henam.	2004/00/02 15:00
_	190	430/033.0018.	USPAT; US-PGPUB;	2004/09/03 15:02
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1984	438/637.ccls.	USPĀT;	2004/09/03 15:04
		100,000,000	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	28716	submicron or sublithograph\$8 or submi?cron	USPAT;	2004/09/03 17:41
		or sub?lithograph\$8	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6152289	opening or hole or aperture or via	USPAT;	2004/09/03 17:42
ļ			US-PGPUB;	
}			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1092	(submicron or sublithograph\$8 or	USPĀT;	2004/09/03 17:42
		submi?cron or sub?lithograph\$8) near5	US-PGPUB;	
		(opening or hole or aperture or via)	EPO; JPO;	
		•	DERWENT;	
		(authorizana an authlitheannach 60	IBM_TDB	2004/00/02 17:45
-	559	(submicron or sublithograph\$8 or	USPAT;	2004/09/03 17:45
		submi?cron or sub?lithograph\$8) near4 (via	US-PGPUB;	
		or (contact adj2 (opening or hole or aperture)))	EPO; JPO; DERWENT;	
1		apercure///	IBM TDB	
l _	7981879	 sidewall or wall or side or spacer or edge	USPAT;	2004/09/03 17:46
	.5010,5	Sinch all of blue of spacer of edge	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	•		IBM TDB	
-	408	((submicron or sublithograph\$8 or	USPAT;	2004/09/03 17:47
		submi?cron or sub?lithograph\$8) near4 (via	US-PGPUB;	
		or (contact adj2 (opening or hole or	EPO; JPO;	
		aperture)))) and (sidewall or wall or side	DERWENT;	
		or spacer or edge)	IBM_TDB	
[-	1	6441430.pn.	USPAT	2004/09/06 14:18
_	2	6441430.pn.	USPAT;	2004/09/06 14:18
			US-PGPUB;	
			EPO;	
	L		DERWENT	<u></u>

_	918	438/95.ccls.	USPAT;	2004/09/06 14:20
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	3056117	oxidi\$5 or oxidat\$4 or nitridi\$4 or	USPAT;	2004/09/06 14:22
	3030117	nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	2004,03,00 11.22
		fluorinat\$4 or transform\$4 or convert\$4	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	214		USPĀT;	2004/09/06 14:22
		nitridi\$4 or nitridat\$4 or nitrided or	US-PGPUB;	
		hydrogenat\$4 or fluorinat\$4 or transform\$4	EPO; JPO;	
		or convert\$4)	DERWENT;	
	727	438/595.ccls.	<pre>IBM_TDB USPAT;</pre>	2004/09/06 15:16
	'2'	4307393.0013.	US-PGPUB;	2004/03/00 13:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4171	dummy near6 gate	USPĀT;	2004/09/06 15:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	34	438/595.ccls. and (dummy near6 gate)	IBM_TDB USPAT;	2004/09/06 15:36
-	34	438/393.0018. and (dummy hears gate)	US-PGPUB;	2004/03/00 13.30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2255	dummy adj3 gate	USPĀT;	2004/09/06 15:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	922520	oxidi\$5 or oxidat\$4 or nitridi\$4 or	IBM_TDB USPAT;	2004/09/06 15:37
-	922320	nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	2004/09/00 13:37
		fluorinat\$4	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
_	5307156	aluminum or al or copper or cu or silicon	USPAT;	2004/09/06 15:38
		or si or polysi or polysilicon or (poly or	US-PGPUB;	
		polycrystal\$4) adj2 (si or silicon)	EPO; JPO;	
			DERWENT; IBM TDB	
	270947	(oxidi\$5 or oxidat\$4 or nitridi\$4 or	USPAT;	2004/09/06 15:39
	2/034/	nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	2001,00,00 20.00
		fluorinat\$4) same (aluminum or al or	EPO; JPO;	
		copper or cu or silicon or si or polysi or	DERWENT;	
		polysilicon or (poly or polycrystal\$4)	IBM_TDB	
		adj2 (si or silicon))	riana.	0004/00/05 15:00
-	589		USPAT;	2004/09/06 15:39
		oxidat\$4 or nitridi\$4 or nitridat\$4 or nitrided or hydrogenat\$4 or fluorinat\$4)	US-PGPUB; EPO; JPO;	
		same (aluminum or al or copper or cu or	DERWENT;	
		silicon or si or polysi or polysilicon or	IBM TDB	
		(poly or polycrystal\$4) adj2 (si or	_	
1		silicon)))		
-	7284121	sidewall or wall or side or spacer	USPAT;	2004/09/06 15:40
	1		US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT; IBM TDB	
_	555	((dummy adj3 gate) and ((oxidi\$5 or	USPAT;	2004/09/06 15:40
		oxidat\$4 or nitridi\$4 or nitridat\$4 or	US-PGPUB;	
	1	nitrided or hydrogenat\$4 or fluorinat\$4)	EPO; JPO;	
		same (aluminum or al or copper or cu or	DERWENT;	
	1	silicon or si or polysi or polysilicon or	IBM_TDB	
		(poly or polycrystal\$4) adj2 (si or		
		silicon)))) and (sidewall or wall or side		
L	l	or spacer)	L	l

-	187590	(oxidi\$5 or oxidat\$4 or nitridi\$4 or	USPAT;	2004/09/06 15:41
		nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	
		fluorinat\$4) with (aluminum or al or	EPO; JPO;	
		copper or cu or silicon or si or polysi or	DERWENT;	
		polysilicon or (poly or polycrystal\$4)	IBM TDB	
		adj2 (si or silicon))	_	
-	508	((oxidi\$5 or oxidat\$4 or nitridi\$4 or	USPAT;	2004/09/06 15:44
		nitridat\$4 or nitrided or hydrogenat\$4 or	US-PGPUB;	
		fluorinat\$4) with (aluminum or al or	EPO; JPO;	
		copper or cu or silicon or si or polysi or	DERWENT;	
		polysilicon or (poly or polycrystal\$4)	IBM TDB	
		adj2 (si or silicon))) and (dummy adj3	_ _	
		gate)		
-	1900986		USPAT;	2004/09/06 15:46
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
_	68225	dummy	USPAT;	2004/09/06 15:47
	00220	Canaly	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	358	(aluminum or al or copper or cu or silicon	USPAT;	2004/09/06 15:47
		or si or polysi or polysilicon or (poly or	US-PGPUB;	
		polycrystal\$4) adj2 (si or silicon)) with	EPO; JPO;	
		(wire or interconnect\$4) with dummy	DERWENT;	
		(of interconnectifi,	IBM TDB	
_	2635131	contact adj3 (opening or hole or aperture)	USPAT;	2004/09/06 15:48
	-000101	or via	US-PGPUB;	=====, ==, == =======================
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	193	((aluminum or al or copper or cu or	USPAT;	2004/09/06 15:49
	1/3	silicon or si or polysi or polysilicon or	US-PGPUB;	
		(poly or polycrystal\$4) adj2 (si or	EPO; JPO;	1
		silicon)) with (wire or interconnect\$4)	DERWENT;	
		with dummy) and (contact adj3 (opening or	IBM TDB	
]		hole or aperture) or via)	1511-155	
	I	Inote of abeliate, of via)	l	